



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

KTC4377 TRANSISTOR (NPN)

FEATURES

Low voltage

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

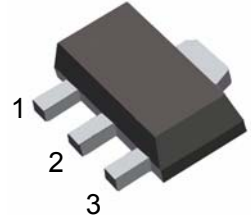
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	10	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	2	A
P_C	Collector Power Dissipation	0.5	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	10			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=0.5\text{A}$	140		600	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=2\text{A}$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=50\text{mA}$			0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=1\text{V}, I_C=2\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE}=1\text{V}, I_C=0.5\text{A}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		27		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	A	B	C	D
Range	140-240	200-330	300-450	420-600
Marking	SA	SB	SC	SD

Typical Characteristics

KTC4377

